

Title (en)

ARRANGEMENT WITH P-DOPED AND N-DOPED SEMICONDUCTOR LAYERS AND METHOD FOR PRODUCING THE SAME

Title (de)

ANORDNUNG MIT P-DOTIERTEN UND N-DOTIERTEN HALBLEITERSCHICHTEN SOWIE VERFAHREN ZU DEREN HERSTELLUNG

Title (fr)

DISPOSITIF A COUCHES SEMI-CONDUCTRICES DOPEES P ET DOPEES N ET SON PROCEDE DE FABRICATION

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Application

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Abstract (en)

[origin: WO0203473A1] The invention relates to an arrangement with P-doped semiconductor layers (12) and N-doped semiconductor layers (14, 10). Said arrangement has junctions between said P-doped semiconductor layers (12) and said N-doped semiconductor layers (14, 10), these junctions showing a Zener breakdown when a characteristic voltage for a junction is applied. A plurality of junctions are present between the P-doped semiconductor layers (12) and the N-doped semiconductor layers (14, 10) and the characteristic voltages enter additively into the breakdown voltage of the arrangement overall. The invention also relates to a method for producing an inventive arrangement.

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